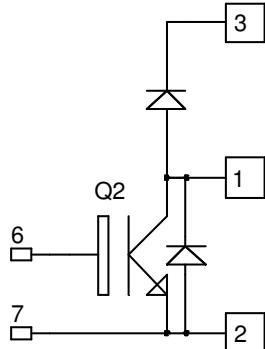


Boost chopper *Trench IGBT® Power Module*

V_{CES} = 1200V
I_C = 25A @ T_c = 80°C



Application

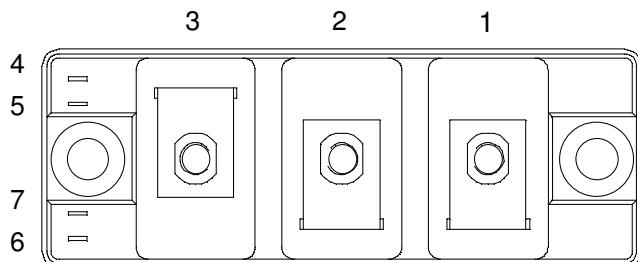
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage	1200	V
I _C	Continuous Collector Current	T _c = 25°C	A
		T _c = 80°C	
I _{CM}	Pulsed Collector Current	T _c = 25°C	65
V _{GE}	Gate – Emitter Voltage	±20	V
P _D	Maximum Power Dissipation	T _c = 25°C	140
RBSOA	Reverse Bias Safe Operation Area	T _j = 125°C	50A@1200V

 CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{\text{GE}} = 0\text{V}, I_{\text{C}} = 4\text{mA}$		1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 1200\text{V}$				5	mA
$V_{\text{CE}(\text{on})}$	Collector Emitter on Voltage	$V_{\text{GE}} = 15\text{V}$	$T_j = 25^\circ\text{C}$		1.7	2.1	V
		$I_{\text{C}} = 25\text{A}$	$T_j = 125^\circ\text{C}$		2.0		
$V_{\text{GE}(\text{th})}$	Gate Threshold Voltage	$V_{\text{GE}} = V_{\text{CE}}, I_{\text{C}} = 1\text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{\text{GE}} = 20\text{V}, V_{\text{CE}} = 0\text{V}$				400	nA

Dynamic Characteristics

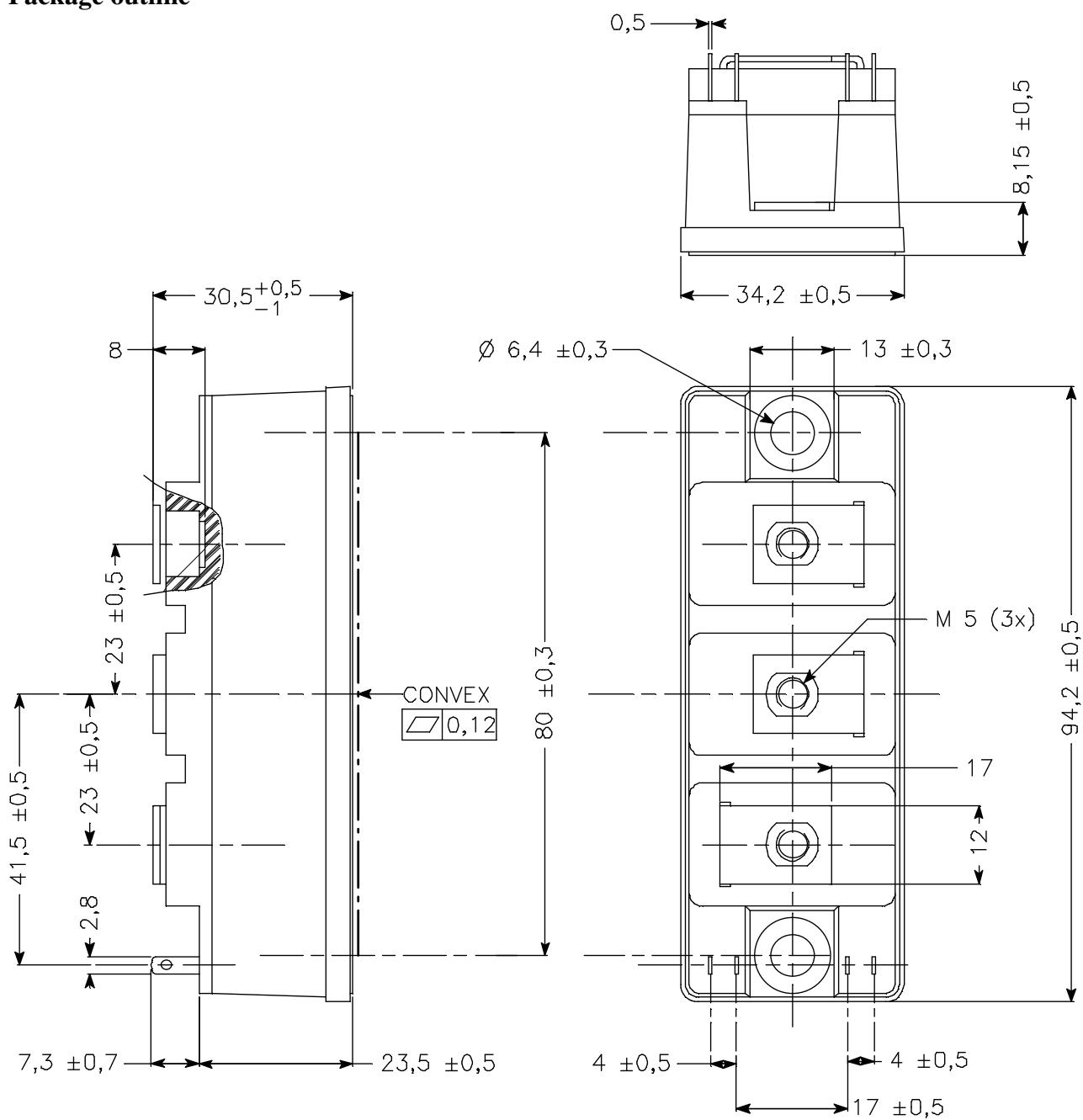
<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{\text{GE}} = 0\text{V}$ $V_{\text{CE}} = 25\text{V}$ $f = 1\text{MHz}$			1.8		nF
C_{oes}	Output Capacitance				0.1		
C_{res}	Reverse Transfer Capacitance				0.08		
$T_{\text{d}(\text{on})}$	Turn-on Delay Time	$\text{Inductive Switching } (25^\circ\text{C})$ $V_{\text{GE}} = \pm 15\text{V}$ $V_{\text{Bus}} = 600\text{V}$ $I_{\text{C}} = 25\text{A}$ $R_G = 36\Omega$		150			ns
T_r	Rise Time			90			
$T_{\text{d}(\text{off})}$	Turn-off Delay Time			550			
T_f	Fall Time			130			
$T_{\text{d}(\text{on})}$	Turn-on Delay Time	$\text{Inductive Switching } (125^\circ\text{C})$ $V_{\text{GE}} = \pm 15\text{V}$ $V_{\text{Bus}} = 600\text{V}$ $I_{\text{C}} = 25\text{A}$ $R_G = 36\Omega$		180			ns
T_r	Rise Time			100			
$T_{\text{d}(\text{off})}$	Turn-off Delay Time			650			
T_f	Fall Time			180			

Reverse diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_F	Diode Forward Voltage	$I_F = 25\text{A}$	$T_j = 25^\circ\text{C}$		1.6	2.1	V
		$V_{\text{GE}} = 0\text{V}$	$T_j = 125^\circ\text{C}$		1.6		
E_{rec}	Reverse Recovery Energy	$I_F = 25\text{A}$ $V_R = 600\text{V}$ $\text{di/dt} = 990\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		2		mJ
Q_{rr}	Reverse Recovery Charge	$I_F = 25\text{A}$ $V_R = 600\text{V}$ $\text{di/dt} = 990\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		2.7		μC
			$T_j = 125^\circ\text{C}$		5		

Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R_{thJC}	Junction to Case	IGBT		0.9	$^\circ\text{C}/\text{W}$
		Diode		1.5	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$, $I_{\text{isol}} < 1\text{mA}$, 50/60Hz	2500			V
T_j	Operating junction temperature range	-40		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-40		125	
T_c	Operating Case Temperature	-40		125	
Torque	Mounting torque	For terminals	M5	2	N.m
		To Heatsink	M6	3	
Wt	Package Weight			180	g

Package outline


APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.